

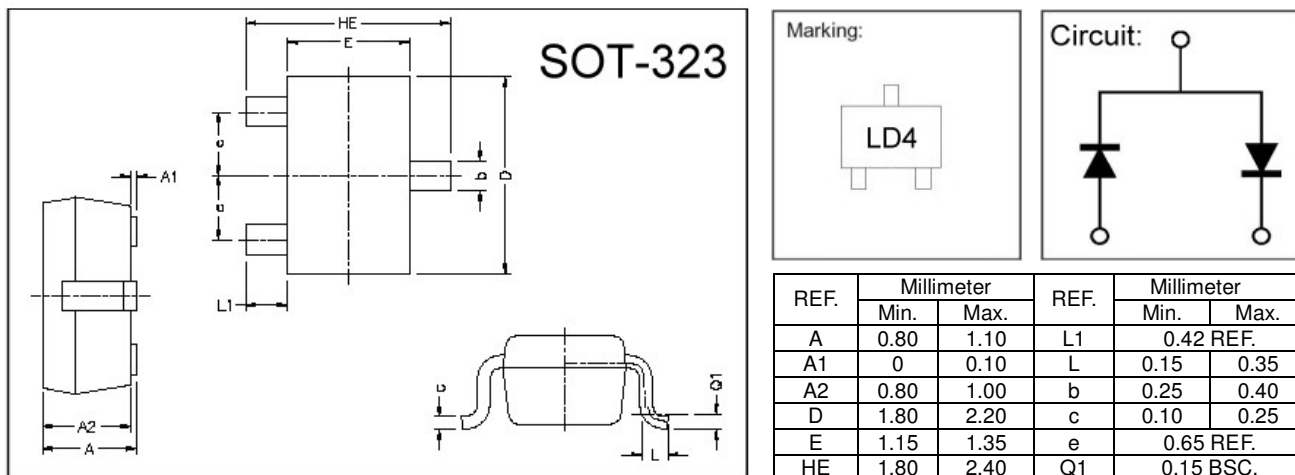
GS706SD

SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 45V, CURRENT 0.03A

Description

The GS706SD is designed for general purpose detection and high speed switching.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _J	+125	°C
Storage Temperature	T _{stg}	-40 ~ +125	°C
Maximum Peak Repetitive Reverse Voltage	V _{RRM}	45	V
Maximum RMS Voltage	V _{RMS}	32	V
Maximum DC Blocking Voltage	V _{DC}	40	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	0.2	A
Typical Junction Capacitance between Terminal (Note 1)	C _J	2.0	pF
Maximum Average Forward Rectified Current	I _o	0.03	A
Total Power Dissipation	PD	225	mW

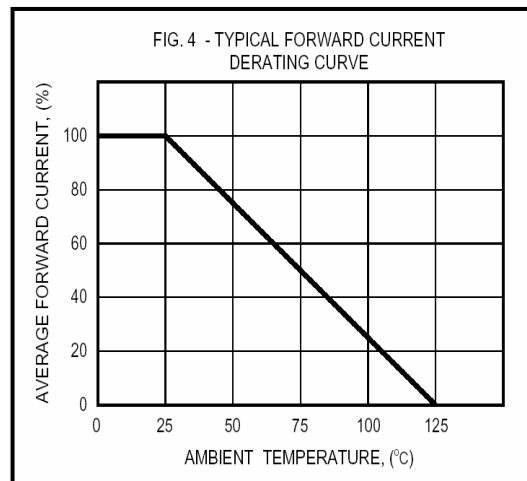
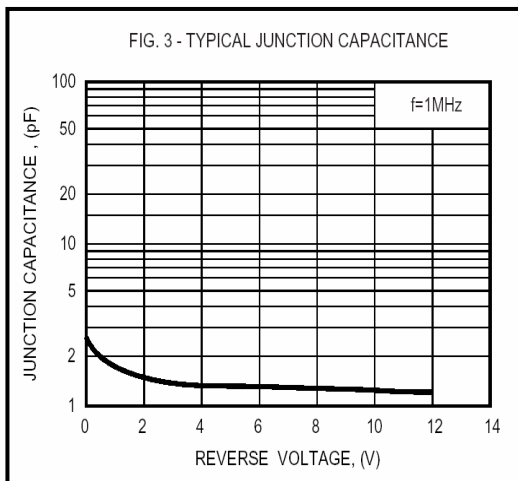
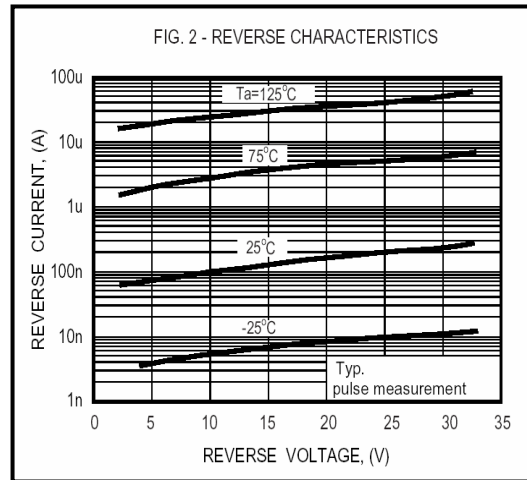
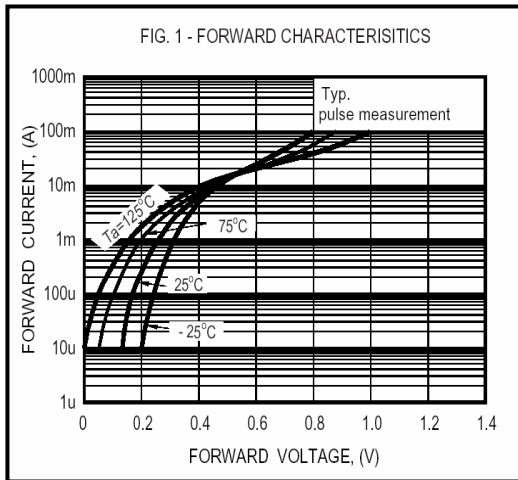
Characteristics at Ta = 25°C

Characteristics	Symbol	Typ.	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V _F	0.37	V	IF = 1mA
Maximum Average Reverse Current	IR	1.0	uA	VR = 10V

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 1.0 volt.

2. ESD sensitive product handling required.

Characteristics Curve



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